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10 a layer of polycrystalline silicon formed over at least said portion of said layer of silicon dioxide into which said hydrogen ions were implanted, said layer of polycrystalline silicon having a smooth morphology; and

a repeating series of gates, sources and drains for at least one field effect transistor formed on each of said plurality of die, said series of gates, sources and drains being formed on said semiconductor substrate.

Q<sup>4</sup>  
14. A thin film transistor comprising:

a semiconductor substrate formed from a material selected from the group consisting of silicon dioxide, quartz and glass, said semiconductor substrate having hydrogen ions implanted therein by plasma source ion implantation;

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a layer of polycrystalline silicon formed on at least a portion of semiconductor substrate, said layer of polycrystalline silicon having a smooth morphology;

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a layer of an insulating material formed on at least a portion of said layer of polycrystalline silicon;

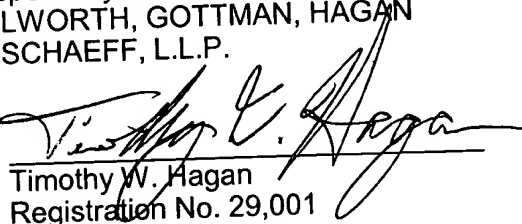
a source region and a drain region formed on said layer of polycrystalline silicon; and  
a gate electrode formed on said layer of insulating material.

REMARKS

Claims 9-12 and 14 were withdrawn from the parent application. Applicant respectfully requests examination of those claims on the merits in this divisional application.

Respectfully submitted,  
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